a current constriction layer for current confinement and light confinement consisting of at least two layers which is disposed in either of said n-type clad layer and said p-type clad layer,

wherein a first layer of said current constriction layer closer to said active layer has a different conductivity type from a conductivity type of either of said clad layers in which said current constriction layer is provided and is made of a material having almost the same refractive index as said clad layer which refractive index is smaller than that of said active layer, and

A1

wherein a second layer of said current constriction layer farther from said active layer is made of a material having a smaller refractive index than said first layer.

3. (Amended) The semiconductor laser of claim 2, wherein said stripe trench is formed so as to have an inclined surface with respect to a width-direction of said current constriction layer, so that a width of said stripe trench for injecting current provided in said first layer is smaller than a width of said stripe trench provided in said second layer.

(unchanged)
A2

5. (Amended) The semiconductor laser of claim 2, wherein said stripe trench in said first layer and said stripe trench in said second layer are provided in different steps, so that the width of said stripe trench provided in said first layer is smaller than the width of said stripe trench provided in said second layer.

(unchanged)
A3

A marked-up copy of the amended claims is attached as required under 37 C.F.R. § 1.121.